TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74ACT573P,TC74ACT573F,TC74ACT573FT

Octal D-Type Latch with 3-State Output

The TC74ACT573 is an advanced high speed CMOS OCTAL LATCH fabricated with silicon gate and double-layer metal wiring C^2MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels.

These 8-bit D-type latches are controlled by a latch enable (LE) and a output enable input (\overline{OE}) .

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

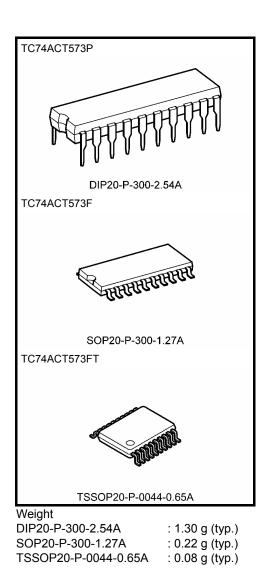
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Features

- High speed: $t_{pd} = 5.5 \text{ ns}$ (typ.) at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 8 \mu A \pmod{at Ta} = 25^{\circ}C$
- Compatible with TTL outputs: VIL = 0.8 V (max)

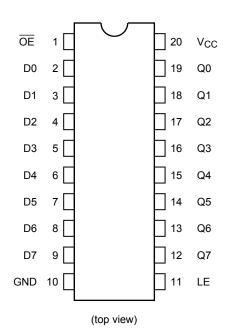
 $V_{IH} = 2.0 V (min)$

- Symmetrical output impedance: $|I_{OH}| = I_{OL} = 24$ mA (min) Capability of driving 50 Ω transmission lines.
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Pin and function compatible with 74F573



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Pin Assignment



IEC Logic Symbol

OE(1) LE(11)	EN C1	
D0 (2)	1D ⊳ ∿	<u>(19)</u> Q0
D1 (3)		(18) (17) Q1
D2(5)		(17) Q2 (16) Q2
D3 (5) D4 (6)		(15) Q3 (15) Q4
D5 <u>(7)</u>		<u>(14)</u> Q5
D6 <u>(8)</u>		(13) Q6
D7 <u>(9)</u>		<u>(12)</u> Q7

Truth Table

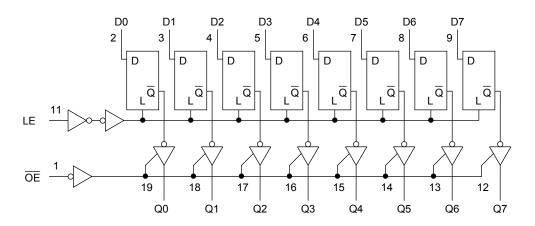
	Inputs	Output			
ŌĒ	LE	D	Q		
Н	Х	Х	Z		
L	L	Х	Qn		
L	Н	L	L		
L	Н	Н	Н		

X: Don't care

Z: High impedance

 $\mathsf{Q}_n:\mathsf{Q}$ outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5 to 7.0	V
DC input voltage	VIN	-0.5 to V _{CC} + 0.5	V
DC output voltage	V _{OUT}	-0.5 to V _{CC} + 0.5	V
Input diode current	I _{IK}	±20	mA
Output diode current	IOK	±50	mA
DC output current	IOUT	±50	mA
DC V _{CC} /ground current	ICC	±200	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP/TSSOP)	mW
Storage temperature	T _{stg}	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65° C. From Ta = 65 to 85° C a derating factor of -10 mW/°C should be applied up to 300 mW.

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	4.5 to 5.5	V
Input voltage	V _{IN}	0 to V _{CC}	V
Output voltage	V _{OUT}	0 to V _{CC}	V
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	dt/dV	0 to 10	ns/V

Operating Ranges (Note)

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Characteristics Symbol		Test Condition			-	Ta = 25°()	Ta = −40 to 85°C		Unit	
					V _{CC} (V)	Min	Тур.	Max	Min	Max	Onit
High-level input voltage	VIH	_			4.5 to 5.5	2.0	_	_	2.0	_	V
Low-level input voltage	VIL	_			4.5 to 5.5	_	_	0.8	_	0.8	V
		V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50 μA		4.5	4.4	4.5		4.4	_	
High-level output voltage	V _{OH}		I _{OH} = −24 mA		4.5	3.94	—	_	3.80	—	V
			I _{OH} = −75 mA	(Note)	5.5	—	—	—	3.85	—	
	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA		4.5	_	0.0	0.1	_	0.1	
Low-level output voltage			I _{OL} = 24 mA		4.5	_	—	0.36	—	0.44	V
			I _{OL} = 75 mA	(Note)	5.5	—	—	—	—	1.65	
3-state output off-state current	I _{OZ}		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or } GND$		5.5	_	—	±0.5		±5.0	μA
Input leakage current	I _{IN}	V _{IN} = V _{CC} or GND		5.5	_	_	±0.1	-	±1.0	μA	
	ICC	$V_{IN} = V_C$	V _{IN} = V _{CC} or GND		5.5	_	_	8.0	_	80.0	μA
Quiescent supply current IC		Per input: V _{IN} = 3.4 V Other input: V _{CC} or GND			5.5		_	1.35	_	1.5	mA

Note: This spec indicates the capability of driving 50 Ω transmission lines.

One output should be tested at a time for a 10 ms maximum duration.

Timing Requirements (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C	Ta = −40 to 85°C	Unit	
			$V_{CC}(V)$	Limit	Limit		
Minimum pulse width (LE)	t _{w (H)}	_	5.0 ± 0.5	5.0	5.0	ns	
Minimum set-up time	ts	_	5.0 ± 0.5	3.0	3.0	ns	
Minimum hold time	t _h	—	5.0 ± 0.5	2.0	2.0	ns	

AC Characteristics (C_L = 50 pF, R_L = 500 Ω , input: t_r = t_f = 3 ns)

Characteristics	Symbol	Test Condition	Ta = 25°0				a = 0 85°C	Unit	
	- ,		V _{CC} (V)	Min	Тур.	Max	Min	Max	
Propagation delay time (LE-Q)	^t pLH ^t pHL	_	5.0 ± 0.5	_	6.3	10.5	1.0	12.0	ns
Propagation delay time (Dn-Q)	t _{pLH} t _{pHL}	_	5.0 ± 0.5	_	6.2	9.6	1.0	11.0	ns
Output enable time	t _{pZL} t _{pZH}	_	5.0 ± 0.5	_	6.5	10.0	1.0	11.5	ns
Output disable time	t _{pLZ} t _{pHZ}	_	5.0 ± 0.5	_	6.5	8.8	1.0	10.0	ns
Input capacitance	C _{IN}	_		_	5	10	_	10	pF
Output capacitance	C _{OUT}	—		_	10	_	_	_	pF
Power dissipation capacitance	C _{PD}		(Note)	_	22	-	_	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$ (per latch)

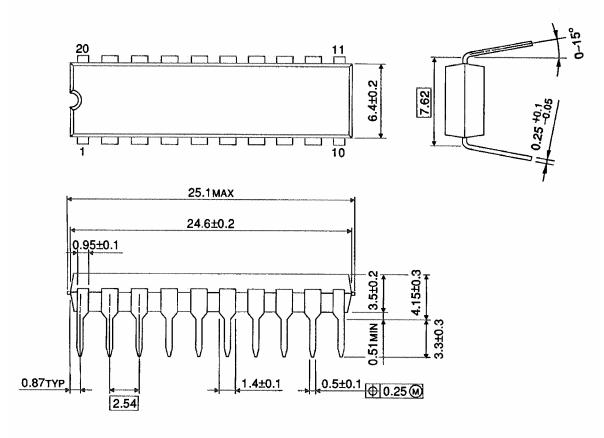
And the total C_{PD} when n pcs. of latch operate can be gained by the following equation:

C_{PD} (total) = 6 + 16·n

Package Dimensions

DIP20-P-300-2.54A

Unit : mm



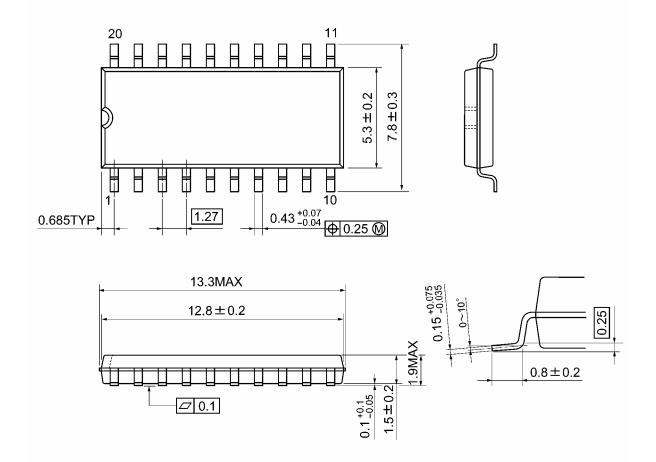
Weight: 1.30 g (typ.)

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Package Dimensions

SOP20-P-300-1.27A

Unit: mm



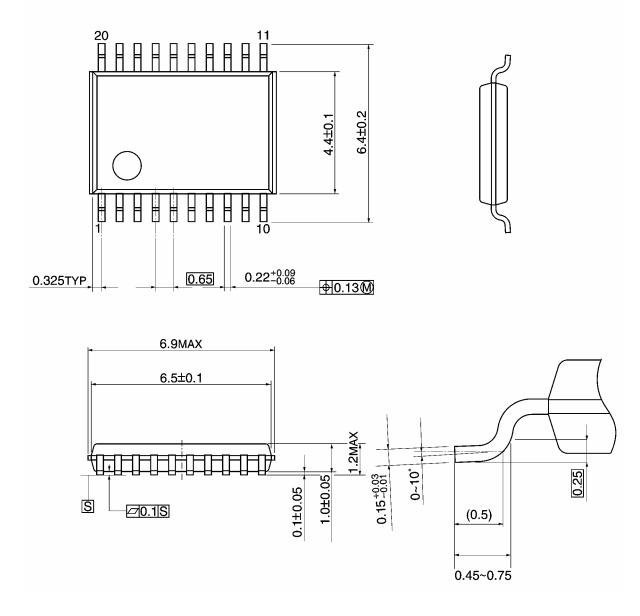
Weight: 0.22 g (typ.)

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Package Dimensions

TSSOP20-P-0044-0.65A

Unit: mm



Weight: 0.08 g (typ.)

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20070701-EN GENERAL

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